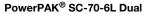
COMPLIANT

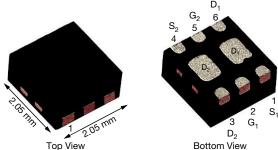
HALOGEN

FREE



Dual P-Channel 30 V (D-S) MOSFET





Marking code: DN

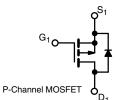
PRODUCT SUMMARY										
V _{DS} (V)	-30									
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -10 \text{ V}$	0.064									
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -4.5 \text{ V}$	0.078									
$R_{DS(on)}$ max. (Ω) at $V_{GS} = -2.5 \text{ V}$	0.120									
Q _g typ. (nC)	6.6									
I _D (A) ^a	-4.5									
Configuration	Dual									

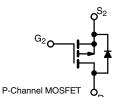
FEATURES

- TrenchFET® Gen III power MOSFET
- Thermally enhanced PowerPAK® SC-70 package
 - Small footprint area
 - Low on-resistance
- 100 % R_q tested
- · Material categorization: for definitions of compliance please see www.vishav.com/doc?99912

APPLICATIONS

- · Load switch and battery management for smart phones, tablet PCs, and portable media players
- Fast battery charging





ORDERING INFORMATION							
Package	PowerPAK SC-70						
Lead (Pb)-free and halogen-free	SiA929DJ-T1-GE3						

ABSOLUTE MAXIMUM RATINGS ($T_A = 25 ^{\circ}C$, unless	s otherwise note	ed)				
PARAMETER		SYMBOL	LIMIT	UNIT			
Drain-source voltage		V _{DS}	-30	V			
Gate-source voltage		V_{GS}	V _{GS} ± 12				
	T _C = 25 °C		-4.5 ^a				
Continuous drain ourrent (T = 150 °C)	T _C = 70 °C		-4.5 ^a				
Continuous drain current (T _J = 150 °C)	T _A = 25 °C	l _D	-4.3 ^{b, c}				
	T _A = 70 °C		-3.4 ^{b, c}	A			
Pulsed drain current (t = 300 μs)		I _{DM}	-15				
Continuous source-drain diode current	T _C = 25 °C		-4.5 ^a				
Continuous source-drain diode current	T _A = 25 °C	l _s	-1.6 ^{b, c}				
	T _C = 25 °C		7.8				
Maximum navvar dissination	T _C = 70 °C		5	W			
Maximum power dissipation	T _A = 25 °C	P _D	1.9 b, c	vv			
	T _A = 70 °C		1.2 ^{b, c}				
Operating junction and storage temperature ran	ige	T _J , T _{stg}	-55 to +150	°C			
Soldering recommendations (peak temperature)) d, e		260				

THERMAL RESISTANCE RATINGS									
PARAMETER	SYMBOL	TYPICAL	MAXIMUM	UNIT					
Maximum junction-to-ambient b, f	junction-to-ambient b, f $t \le 5 s$				°C/W				
Maximum junction-to-case (drain)	Steady state	R_{thJC}	12.5	16	0/ ٧٧				

Notes

- a. Package limited
- b. Surface mounted on 1" x 1" FR4 board
- See solder profile (www.vishay.com/doc?73257). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components
- Maximum under steady state conditions is 110 °C/W



Vishay Siliconix

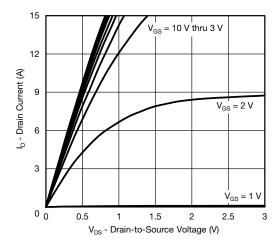
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static	1					1	
Drain-source breakdown voltage	V_{DS}	$V_{GS} = 0 \text{ V}, I_{D} = -250 \mu\text{A}$	-30	-	-	V	
V _{DS} temperature coefficient	$\Delta V_{DS}/T_{J}$			-23	-	140	
V _{GS(th)} temperature coefficient	ΔV _{GS(th)} /T _J	$I_D = -250 \mu A$	-	1.5	-	mV/°C	
Gate-source threshold voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.6	-	-1.1	V	
Gate-source leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$	-	-	± 100	nA	
Zana and a self-and advantage and a		$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	-1	_	
Zero gate voltage drain current	I _{DSS}	$V_{DS} = -30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$	-	-	-10	μA	
On-state drain current a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	-10	-	-	Α	
	, ,	$V_{GS} = -10 \text{ V}, I_D = -3 \text{ A}$	-	0.052	0.064		
Drain-source on-state resistance ^a	R _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -2 \text{ A}$	-	0.062	0.078	Ω	
	, ,	$V_{GS} = -2.5 \text{ V}, I_D = -1 \text{ A}$	-	0.090	0.120		
Forward transconductance a	9 _{fs}	$V_{DS} = -15 \text{ V}, I_D = -3 \text{ A}$	-	10	-	S	
Dynamic ^b				•		l	
Input capacitance	C _{iss}		-	575	-		
Output capacitance	Coss	$V_{DS} = -15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	=.	60	-	рF	
Reverse transfer capacitance	C _{rss}		=.	51	-		
		$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_D = -4.3 \text{ A}$	=.	14	21	nC	
Total gate charge	Q_g		_	6.6	10		
Gate-source charge	Q _{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -4.5 \text{ V}, I_{D} = -4.3 \text{ A}$	_	1.2	-		
Gate-drain charge	Q _{ad}		-	1.9	-		
Gate resistance	R _a	f = 1 MHz	1.1	5.5	11	Ω	
Turn-on delay time	t _{d(on)}		_	15	30		
Rise time	t _r	$V_{DD} = -15 \text{ V}, R_1 = 4.4 \Omega,$	_	18	35	- - -	
Turn-off delay time	t _{d(off)}	$I_D \cong -3.4 \text{ A}, V_{GEN} = -4.5 \text{ V}, R_g = 1 \Omega$	_	22	40		
Fall time	t _f	•	_	10	20		
Turn-on delay time	t _{d(on)}		_	5	10	ns	
Rise time	t _r	$V_{DD} = -15 \text{ V}, R_1 = 4.4 \Omega,$	-	- 10	20	1	
Turn-off delay time	t _{d(off)}	1 04AV 10V D 10			40	1	
Fall time	t _f		_	10	20	1	
Drain-Source Body Diode Characterist							
Continuous source-drain diode current	I _S	T _C = 25 °C	_	_	-4.5		
Pulse diode forward current	I _{SM}	<u> </u>	-	-	-15	A	
Body diode voltage	V _{SD}	I _S = -3.4 A, V _{GS} = 0 V	_	-0.89	-1.2	V	
Body diode reverse recovery time	t _{rr}	.39-03	_	20	40	ns	
Body diode reverse recovery time	Q _{rr}	$I_F = -3.4 \text{ A, di/dt} = 100 \text{ A/}\mu\text{s,}$	_	10	20	nC	
Reverse recovery fall time		$T_{1} = 25 ^{\circ}\text{C}$	_	9	-	ns	
riovorse recevery ran time	t _a	U	_	11	-		

Notes

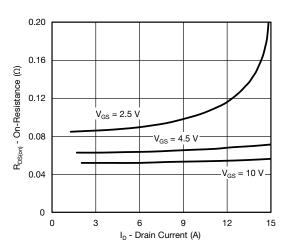
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

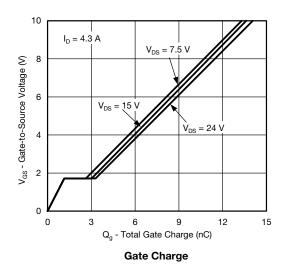


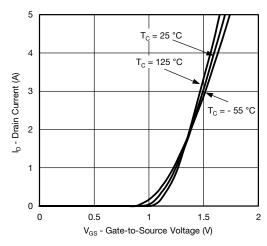


Output Characteristics

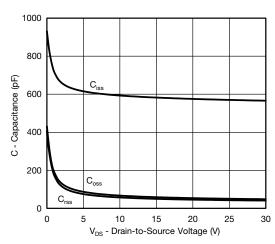


On-Resistance vs. Drain Current and Gate Voltage

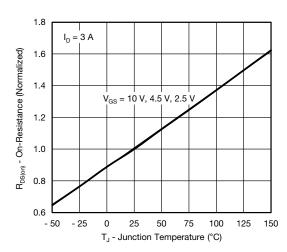




Transfer Characteristics

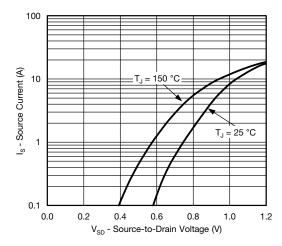


Capacitance

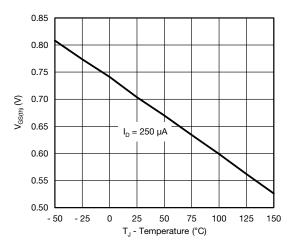


On-Resistance vs. Junction Temperature

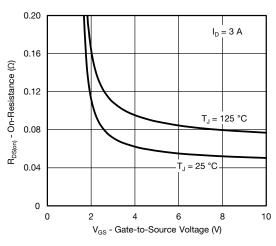




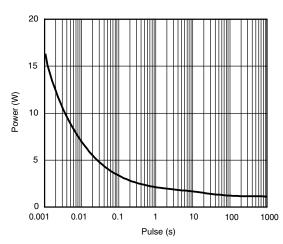
Source-Drain Diode Forward Voltage



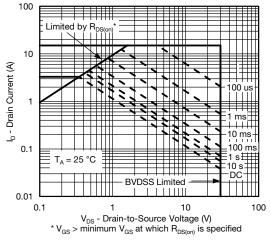
Threshold Voltage



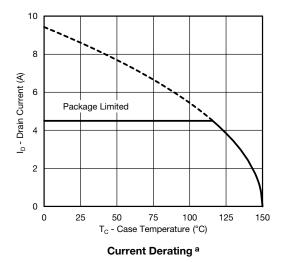
On-Resistance vs. Gate-to-Source Voltage

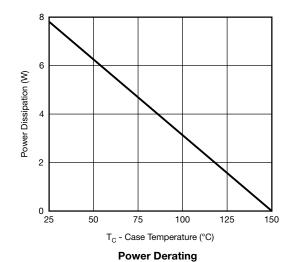


Single Pulse Power, Junction-to-Ambient





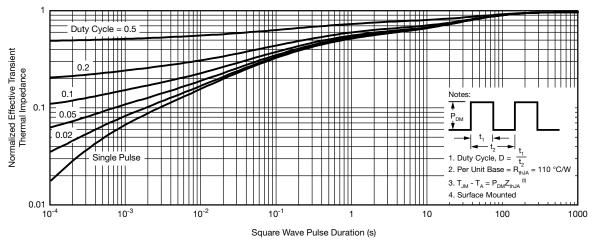




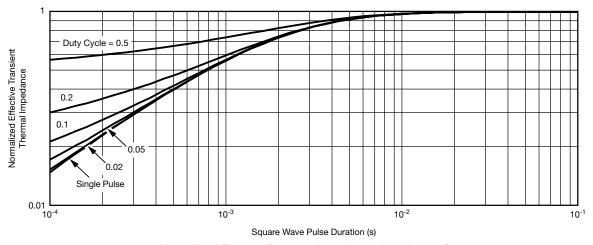
Note

a. The power dissipation P_D is based on T_J max. = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

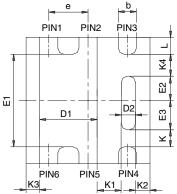
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63398.

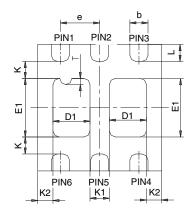




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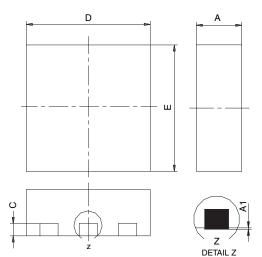
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

	SINGLE PAD						DUAL PAD					
DIM	M	ILLIMETER	RS		INCHES		М	MILLIMETERS			INCHES	
	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max	Min	Nom	Max
Α	0.675	0.75	0.80	0.027	0.030	0.032	0.675	0.75	0.80	0.027	0.030	0.032
A 1	0	-	0.05	0	-	0.002	0	-	0.05	0	-	0.002
b	0.23	0.30	0.38	0.009	0.012	0.015	0.23	0.30	0.38	0.009	0.012	0.015
С	0.15	0.20	0.25	0.006	0.008	0.010	0.15	0.20	0.25	0.006	0.008	0.010
D	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
D1	0.85	0.95	1.05	0.033	0.037	0.041	0.513	0.613	0.713	0.020	0.024	0.028
D2	0.135	0.235	0.335	0.005	0.009	0.013						
E	1.98	2.05	2.15	0.078	0.081	0.085	1.98	2.05	2.15	0.078	0.081	0.085
E1	1.40	1.50	1.60	0.055	0.059	0.063	0.85	0.95	1.05	0.033	0.037	0.041
E2	0.345	0.395	0.445	0.014	0.016	0.018						
E3	0.425	0.475	0.525	0.017	0.019	0.021						
е		0.65 BSC			0.026 BSC	;	0.65 BSC			0.026 BSC		
K		0.275 TYP			0.011 TYP	1	0.275 TYP			0.011 TYP		
K1		0.400 TYP			0.016 TYP		0.320 TYP			0.013 TYP		
K2		0.240 TYP		0.009 TYP		0.252 TYP			0.010 TYP			
К3		0.225 TYP		0.009 TYP								
K4		0.355 TYP		0.014 TYP								
L	0.175	0.275	0.375	0.007	0.011	0.015	0.175	0.275	0.375	0.007	0.011	0.015
Т							0.05	0.10	0.15	0.002	0.004	0.006
ECN: C O	07/21 Pay C 06 Aug 07											

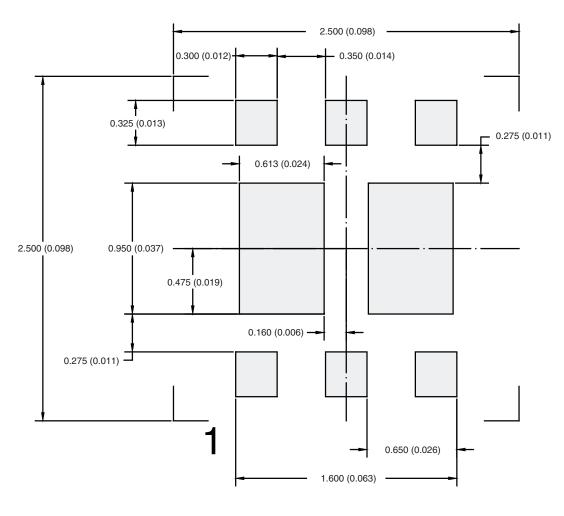
ECN: C-07431 - Rev. C, 06-Aug-07

DWG: 5934

Document Number: 73001 06-Aug-07

VISHAY.

RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Dual



Dimensions in mm (inches)

Return to Index



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Vishay

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